



YJL3134KBW

N-Channel Enhancement Mode Field Effect Transistor



YJL3134KBW

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\text{ H}$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	H
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=10V, V_{DS}=0V$		2.5	10	H
		$V_{GS}=8V, V_{DS}=0V$		500	2000	nA
Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\text{ H}$	0.35	0.75	1.1	V



Typical Performance Characteristics

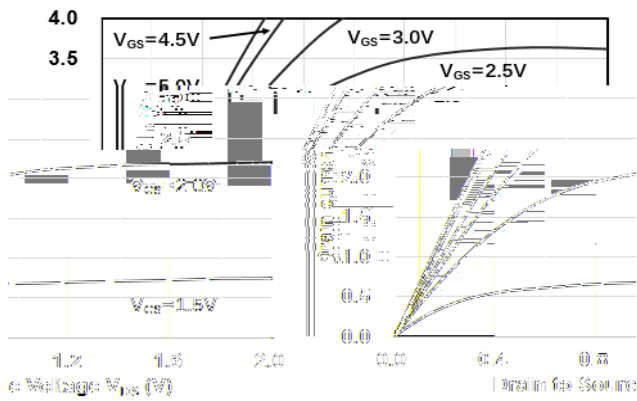


Figure1. Output Characteristics

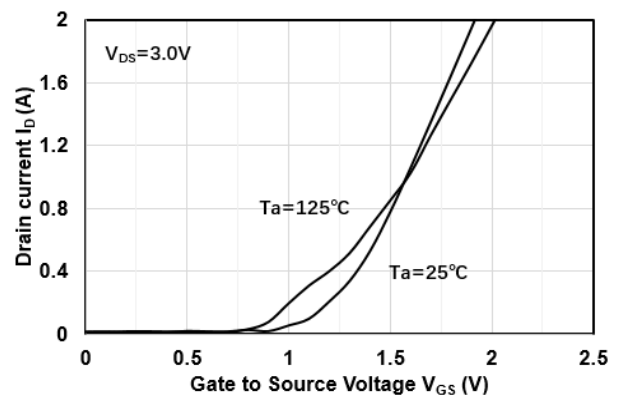


Figure2. Transfer Characteristics

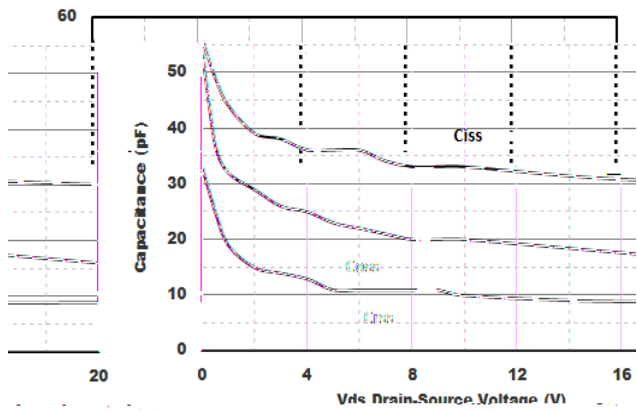


Figure3. Capacitance Characteristics

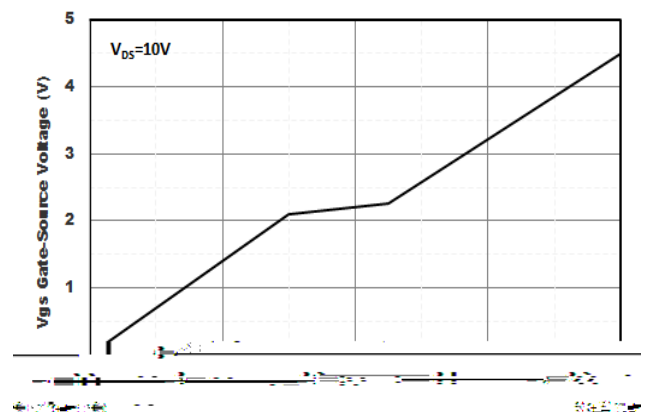


Figure4. Gate Charge

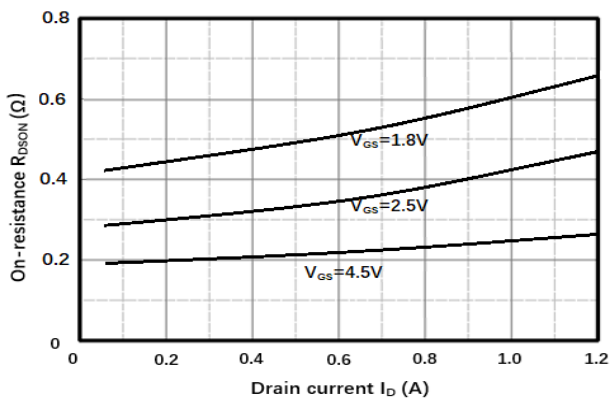


Figure5. Drain-Source on Resistance

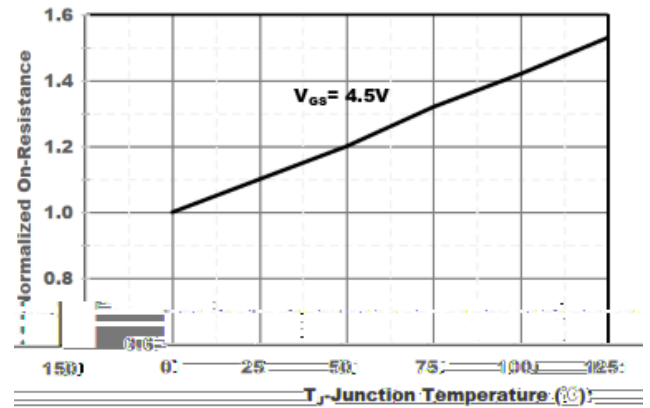


Figure6. Drain-Source on Resistance

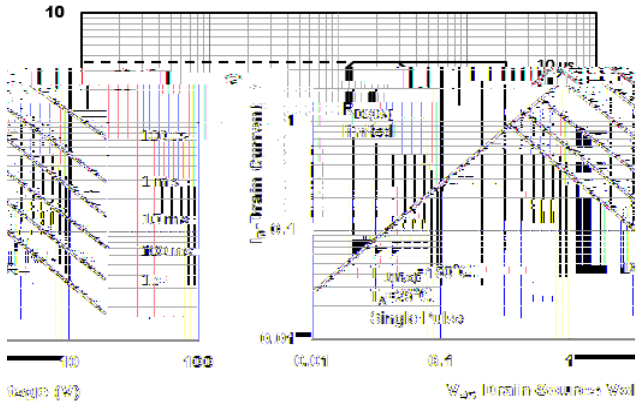


Figure7. Safe Operation Area

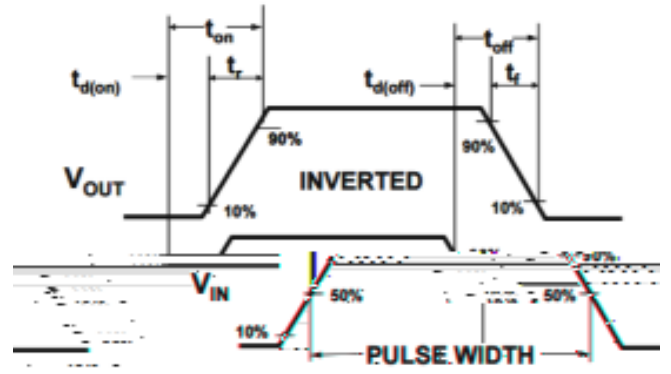


Figure8. Switching wave



YJL3134KBW

SOT-323 Package information

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.043	0.900	1.100
A1	0.000	0.004	0.000	0.100
A2	0.035	0.039	0.900	1.000
b	0.006	0.016	0.150	0.400
c	0.004	0.010	0.100	0.250
D	0.071	0.0	1.800	2.200
E				
E1	0.085	0.095	2.150	2.450

- NOTE:
- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 - 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 - 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



YJL3134KBW

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used w